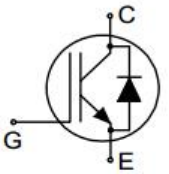
IGBT

Features



- 600V,20A
- $V_{CE(sat)(typ.)}$=1.85V@V_{GE}=15V,I_C=20A
- High speed switching
- Higher system efficiency
- Soft current turn-off waveforms
- Square RBSOA

General Description

JIAEN trench IGBTs offer lower losses and higher energy efficiency for application such as IH (induction heating),UPS, general inverter and other soft switching applications.

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate-Emitter Voltage	± 30	V
I_C	Continuous Collector Current (T_C=25℃)	40	A
	Continuous Collector Current (T_C=100℃)	20	A
I_{CM}	Pulsed Collector Current (Note 1)	60	A
I_F	Diode Continuous Forward Current (T_C=100℃)	20	A
I_{FM}	Diode Maximum Forward Current (Note 1)	60	A
t_{sc}	Short Circuit Withstand Time	10	us
P_D	Maximum Power Dissipation (T_C=25℃)	40	W
	Maximum Power Dissipation (T_C=100℃)	15	W
T_J	Operating Junction Temperature Range	-55 to +150	℃
T_{STG}	Storage Temperature Range	-55 to +150	℃

Thermal Characteristics

Symbol	Parameter	Max.	Units
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to case for IGBT	3.0	℃/ W
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to case for Diode	3.8	℃/ W
$R_{th\ j\text{-}a}$	Thermal Resistance, Junction to Ambient	65	℃/ W

Electrical Characteristics (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{CES}	Collector-Emitter Breakdown Voltage	V_{GE}= 0V, I_C= 250uA	600	-	-	V
I_{CES}	Collector-Emitter Leakage Current	V_{CE}= 600V, V_{GE}= 0V	-	-	100	uA
I_{GES}	Gate Leakage Current, Forward	V_{GE}=30V, V_{CE}= 0V	-	-	100	nA
	Gate Leakage Current, Reverse	V_{GE}= -30V, V_{CE}= 0V	-	-	-100	nA
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE}= V_{CE}, I_C= 250uA	4.5	-	6.5	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	V_{GE}=15V, I_C= 15A	-	1.85	2.3	V
Qg	Total Gate Charge	V_{CC}=400V V_{GE}=15V I_C=20A	-	62		nC
Qge	Gate-Emitter Charge		-	6		nC
Qgc	Gate-Collector Charge		-	33		nC
$t_{d(on)}$	Turn-on Delay Time	V_{CC}=400V V_{GE}=15V I_C=20A R_G=20Ω Inductive Load T_C=25 ℃	-	16	-	ns
t_r	Turn-on Rise Time		-	24	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	122	-	ns
t_f	Turn-off Fall Time		-	35	-	ns
Eon	Turn-on Switching Loss		-	0.43	-	mJ
Eoff	Turn-off Switching Loss		-	0.29	-	mJ
Ets	Total Switching Loss		-	0.72	-	mJ
Cies	Input Capacitance	V_{CE}=25V V_{GE}=0V f = 1MHz	-	920	-	pF
Coes	Output Capacitance		-	150	-	pF
Cres	Reverse Transfer Capacitance		-	54	-	pF

Electrical Characteristics of Diode (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_F	Diode Forward Voltage	I_F=20A	-	1.5	2.3	V
t_{rr}	Diode Reverse Recovery Time	V_{CE} = 300V I_F= 20A dIF/dt = 500A/us	-	90		ns
I_{rr}	Diode peak Reverse Recovery Current		-	19		A
Q_{rr}	Diode Reverse Recovery Charge		-	732		nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

Typical Performance Characteristics

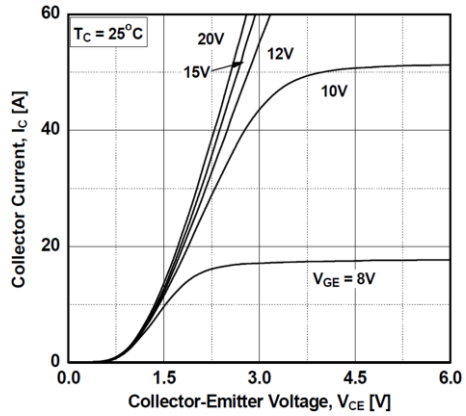


Fig 1. Output characteristics

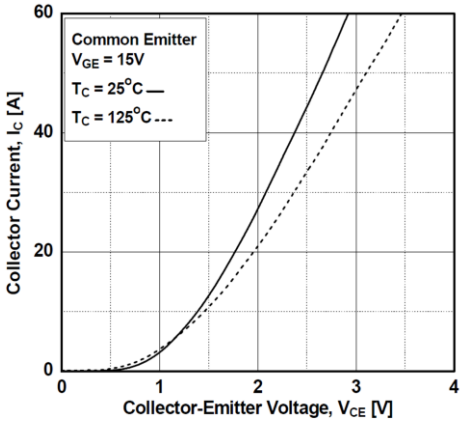


Fig 2. Typical Saturation Voltage Characteristics

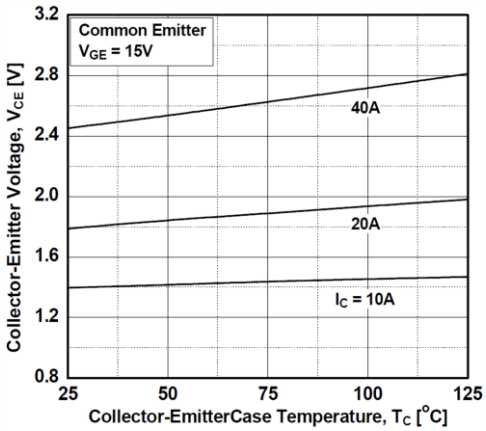


Figure 3. Saturation Voltage vs. Case Temperature

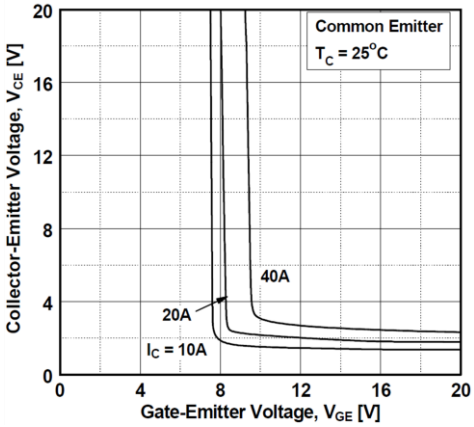


Figure 4. Saturation Voltage vs. VGE

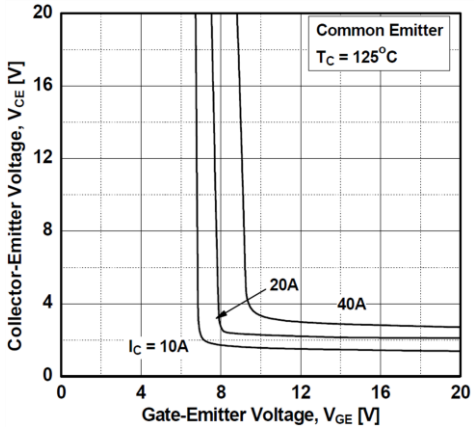


Figure 5. Saturation Voltage vs. VGE

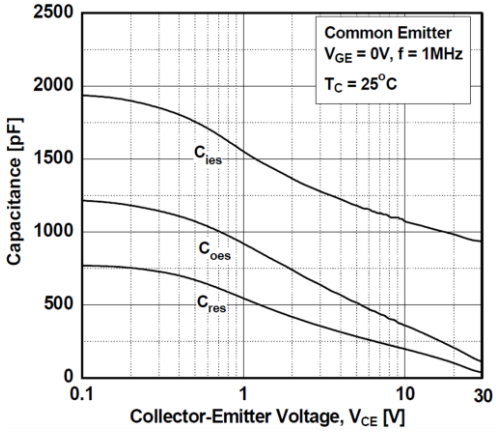


Figure 6. Capacitance Characteristics

Typical Performance Characteristics

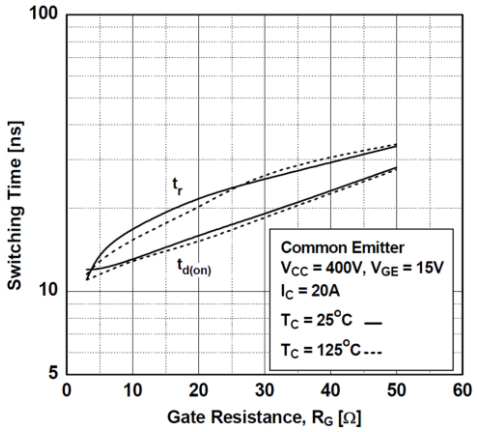


Figure 7. Turn-On Characteristics vs. Gate Resistance

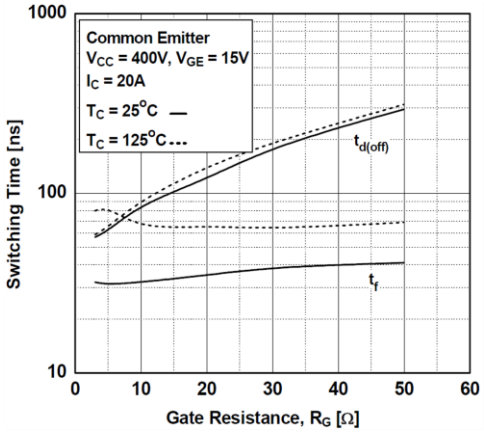


Figure 8. Turn-Off Characteristics vs. Gate Resistance

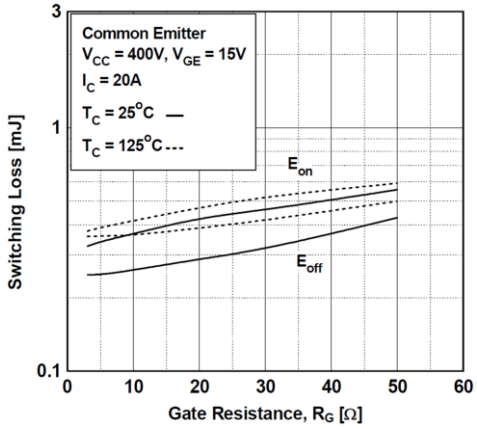


Figure 9. Switching Loss vs. Gate Resistance

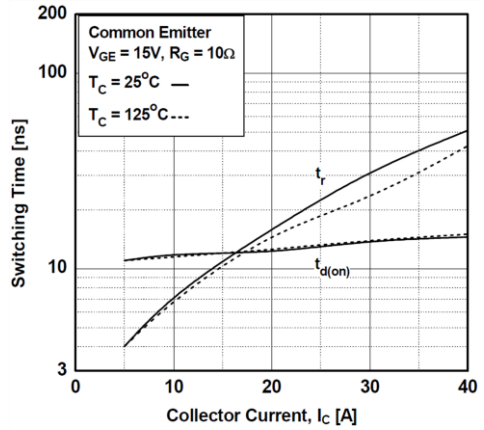


Figure 10. Turn-On Characteristics vs. Collector Current

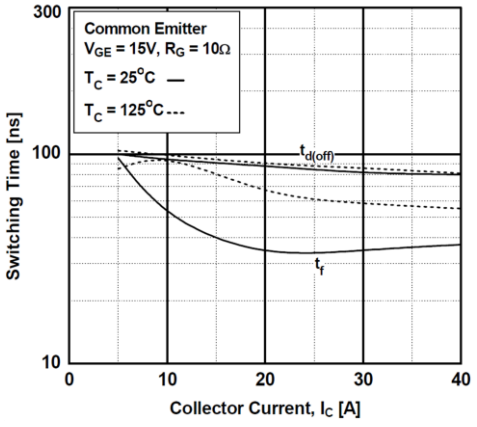


Figure 11. Turn-Off Characteristics vs. Collector Current

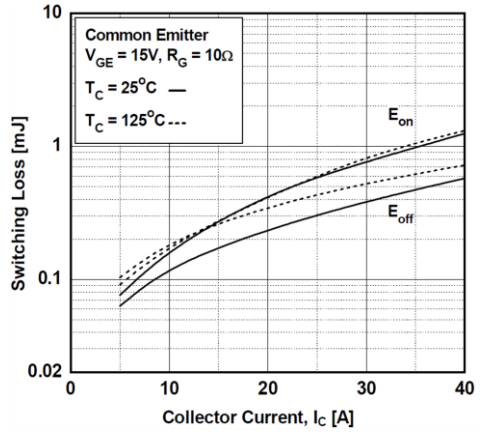


Figure 12. Switching Loss vs. Collector Current

Typical Performance Characteristics

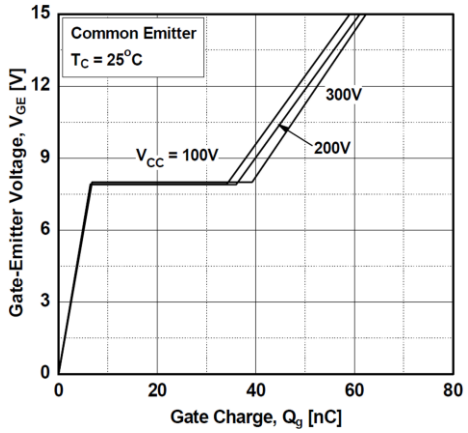


Figure 13. Gate Charge Characteristics

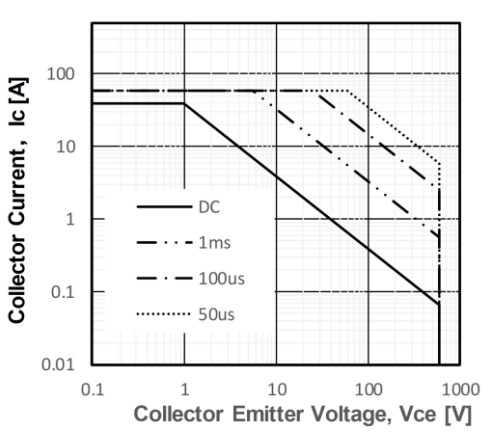


Figure 14. SOA Characteristics

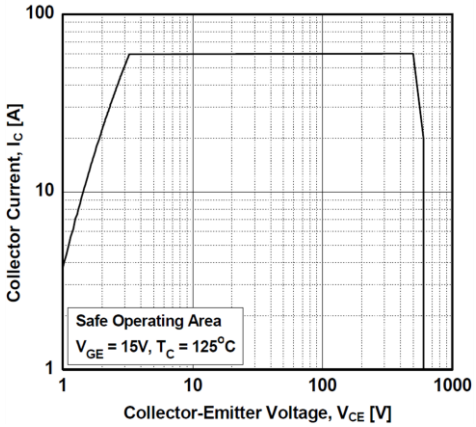


Figure 15. Turn-Off SOA

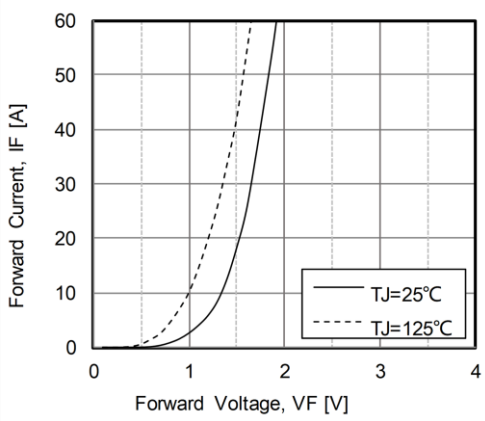


Figure 16. Forward Characteristics

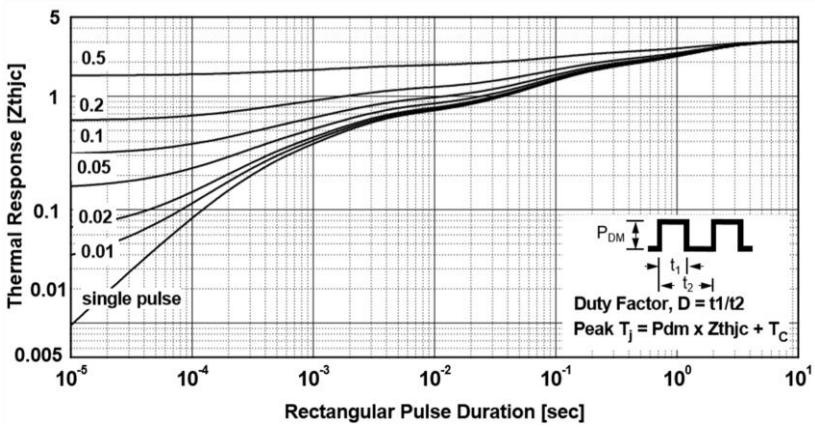
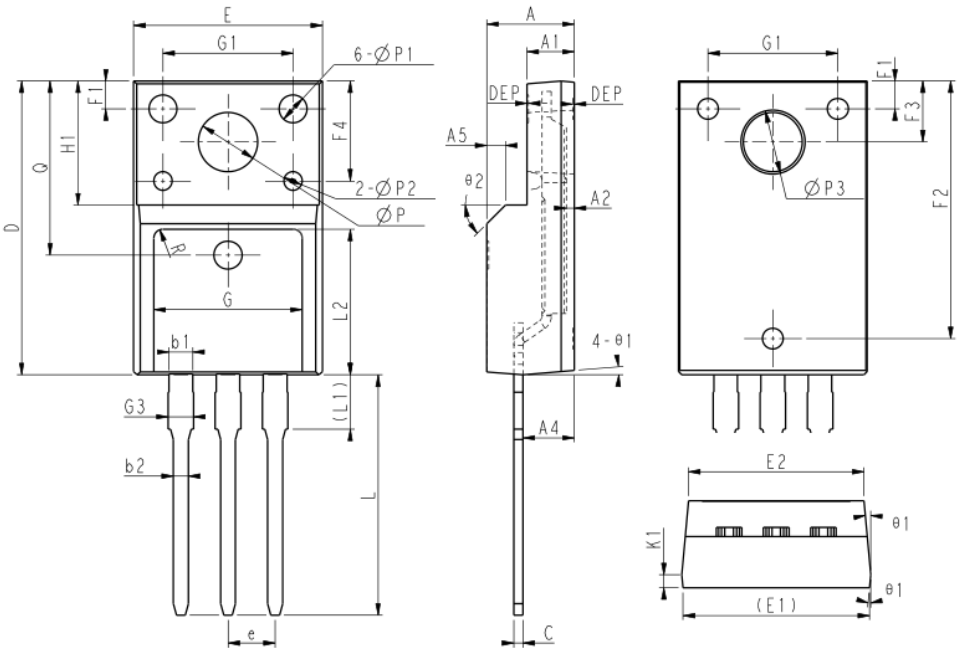


Figure 17. Transient Thermal Impedance of IGBT

Package



COMMON DIMENSIONS

SYMBOL	MM		
	MIN	NOM	MAX
E	10.00	10.16	10.32
E1	9.94	10.04	10.14
E2	9.36	9.46	9.56
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	0.43	–	0.48
A4	2.66	2.76	2.86
A5		1.00REF	
c	0.45	0.50	0.60
D	15.67	15.87	16.07
Q		9.40REF	
H1		6.70REF	
e		2.54BSC	
ΦP		3.18REF	
L	12.78	12.98	13.18
L1	2.83	2.93	3.03
L2	7.70	7.80	7.90
ΦP1	1.40	1.50	1.60
ΦP2	0.95	1.00	1.05
ΦP3		3.45REF	
θ1	3°	5°	7°
θ2	–	45°	–
DEP	0.05	0.10	0.15
F1	1.00	1.50	2.00
F2	13.80	13.90	14.00
F3	3.20	3.30	3.40
F4	5.30	5.40	5.50
G	7.80	8.00	8.20
G1	6.90	7.00	7.10
G3	1.25	1.35	1.45
b1	1.23	1.28	1.38
b2	0.75	0.80	0.90
K1	0.65	0.70	0.75
R		0.50REF	

Disclaimers

JIAEN Semiconductor Co., Ltd reserves the right to make changes without notice in order to improve reliability, function or design and to discontinue any product or service without notice. Customers should obtain the latest relevant information before orders and should verify that such information is current and complete. All products are sold subject to JIAEN's terms and conditions supplied at the time of order acknowledgement.

JIAEN Semiconductor Co., Ltd warrants performance of its hardware products to the specifications at the time of sale, Testing, reliability and quality control are used to the extent JIAEN deems necessary to support this warrantee. Except where agreed upon by contractual agreement, testing of all parameters of each product is not necessarily performed.

JIAEN Semiconductor Co., Ltd does not assume any liability arising from the use of any product or circuit designs described herein. Customers are responsible for their products and applications using JIAEN's components. To minimize risk, customers must provide adequate design and operating safeguards.

JIAEN Semiconductor Co., Ltd does not warrant or convey any license either expressed or implied under its parent rights, nor the rights of others. Reproduction of information in JIAEN's datasheets or data books sis

permissible only if reproduction is without modification or alteration. Reproduction of this information with any alteration is an unfair and deceptive business practice. JIAEN Semiconductor Co., Ltd is not responsible or liable for such altered documentation.

Resale of JIAEN's products with statements different from or beyond the parameters stated by JIAEN Semiconductor Co., Ltd for that product or service voids all express or implied warrantees for the associated JIAEN's product or service and is unfair and deceptive business practice. JIAEN Semiconductor Co., Ltd is not responsible or liable for any such statements.